

Feature

- This module is designed very compactly, Because diode Module and thyristor are put together.
- This module is also isolated type between electorode Terminal and mounting base.

I_D	75A
V_{RRM}	800/1600V
I_{FSM}	0.91/1.0 KA
I^2t	4150 A ² S

Typical application

- Inverter for AC or DC motor control
- Current stabilized power supply
- Switching power supply

● DIODE

■ Maximum Ratings

($T_J=25^\circ\text{C}$)

Symbol	Item	Ratings		Unit
		HDF A75BA80	HDF A75BA160	
V_{RRM}	Repetitive Peak Reverse Voltage	800	1600	V
V_{RSM}	Non-Repetitive Peak Reverse Voltage	960	1700	V

Symbol	Item	Conditions	Ratings	Unit
I_D	Output Current (D.C.)	Three phase full wave, $T_C=117^\circ\text{C}$	75	A
I_{FSM}	Surge forward current	50/60Hz, peak value, non-repetitive	910/1000	A
T_J	Operating Junction Temperature		-40 to +150	$^\circ\text{C}$
T_{stq}	Storage Temperature		-40 to +125	$^\circ\text{C}$
V_{iso}	Isolation Breakdown Voltage (R.M.S.)	R.M.S, $t=1\text{min}$, $I_{iso}: 1\text{mA}(\text{max})$	2500	V
F_M	Mounting (M5)		2.7	N-m
W_t	Mass		150	g

■ Electrical Characteristics

Symbol	Item	Conditions	Ratings	Unit
I_{RRM}	Repetitive Peak Reverse Current, max.	$T_J=150^\circ\text{C}$, $V_{RM}=V_{RRM}$	8	mA
V_{FM}	Forward Voltage Drop, max.	$T_J=25^\circ\text{C}$, $I_F=50\text{A}$	1.30	V
$R_{th(j-c)}$	Thermal Impedance, max.	Junction to Case (TOTAL)	0.25	$^\circ\text{C}/\text{W}$
$R_{th(c-f)}$	Thermal Impedance, max.	Case to Fin	0.10	$^\circ\text{C}/\text{W}$

● THYRISTOR

■ Maximum Ratings

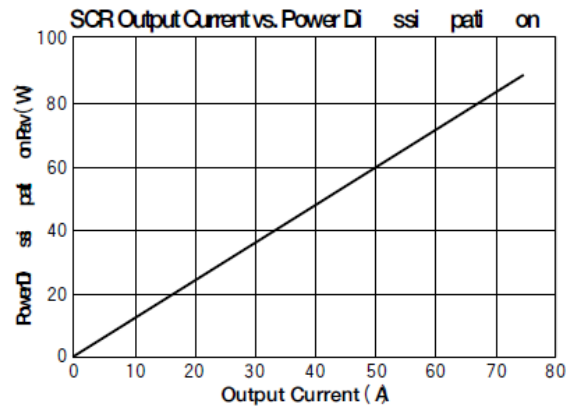
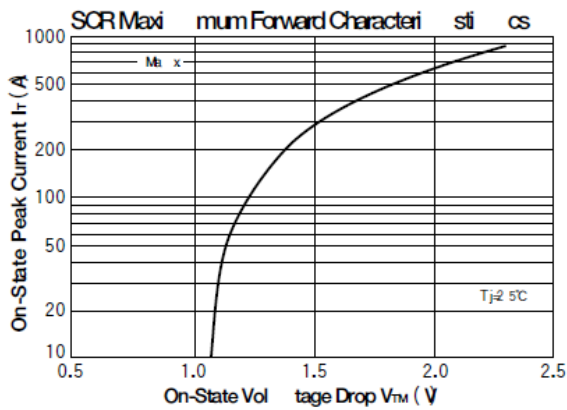
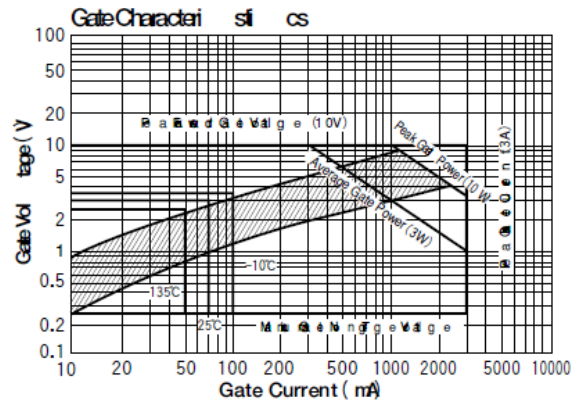
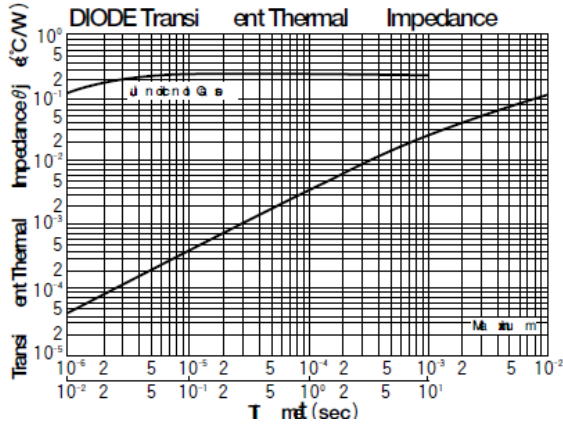
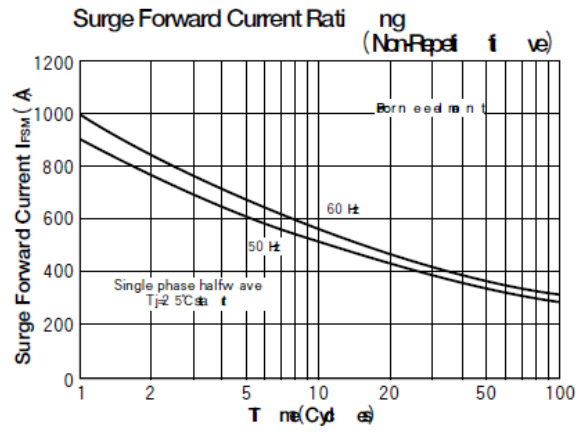
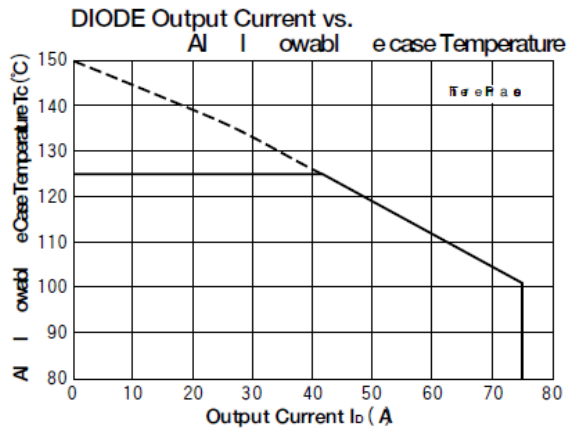
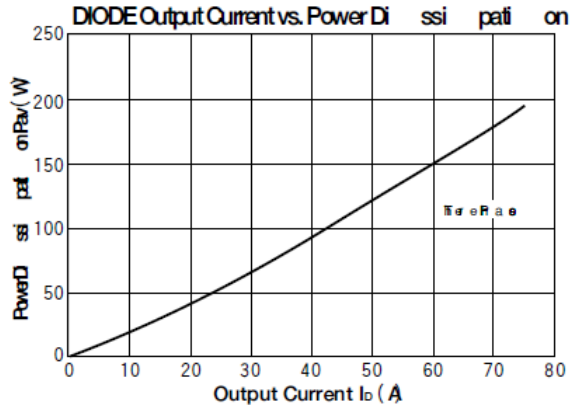
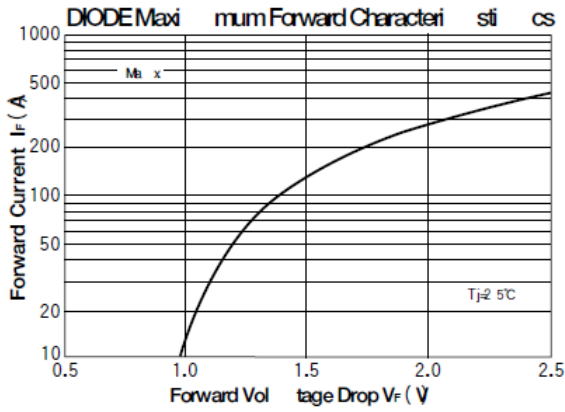
($T_J=25^{\circ}\text{C}$)

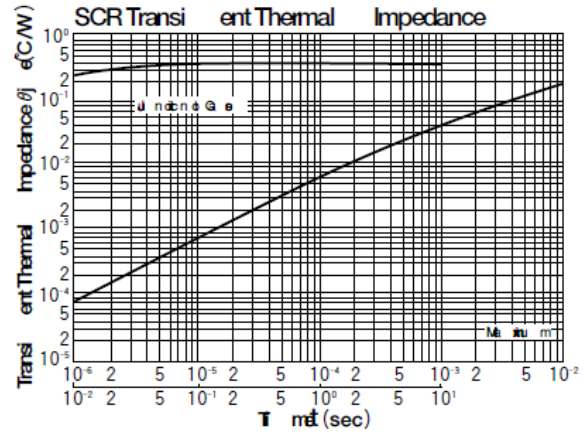
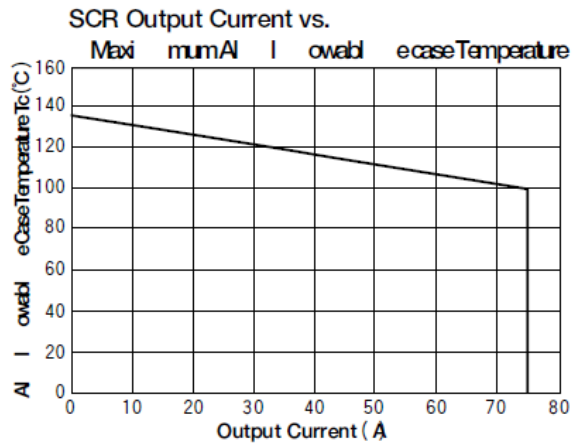
Symbol	Item	Ratings		Unit
		HDF A75BA80	HDF A75BA160	
V_{RRM}	Repetitive Peak Reverse Voltage	800	1600	V
V_{RSM}	Non-Repetitive Peak Reverse Voltage	960	1700	V
V_{DRM}	Repetitive Peak off-State Voltage	800	1600	V

Symbol	Item	Conditions	Ratings	Unit
$I_{T(AV)}$	Average On-State Current	Singl phase half wave.180° conduction, $T_C=85^{\circ}\text{C}$	75	A
I_{TSM}	Surge On-State Current	peak value, non-repetitive, 50/60Hz	910/1000	A
I^2t	I^2t		4150	A^2S
di/dt	Critical Rate of Rise of On-State Current	$I_G=100\text{mA}$, $V_D=1/2V_{DRM}$	150	A/us
V_{iso}	Isolation Breakdown Voltage (R.M.S.)	R.M.S,t=1min, $I_{iso}:1\text{mA}(\text{max})$	2500	V
T_J	Operating Junction Temperature		-40 to +135	$^{\circ}\text{C}$
T_{stq}	Storage Temperature		-40 to +125	$^{\circ}\text{C}$
F_M	Mounting (M5)		2.7	N-m
W_t	Mass		150	g

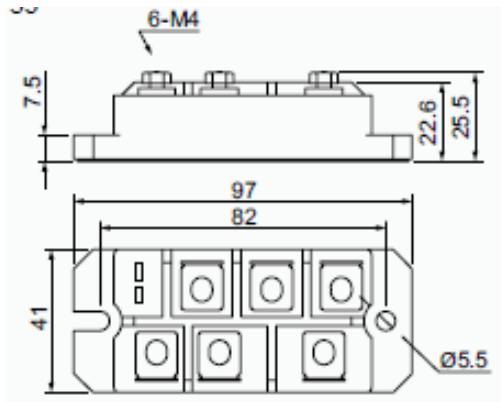
■ Electrical Characteristics

I_{DRM}	Repetitive Peak Off-State Current,max	$T_J=135^{\circ}\text{C}, V_D=V_{DRM}$	60	mA
I_{RRM}	Repetitive Peak Reverse Current,max.	$T_J=135^{\circ}\text{C}, V_D=V_{RRM}$	60	mA
V_{TM}	Peak On-State Voltage,max	$T_J=125^{\circ}\text{C}, I_{TM}=50\text{A}$	1.20	V
I_{GT}	Gate Trigger Current,max	$V_D=6\text{V}, I_A=1\text{A}$	70	mA
V_{GT}	Gate Trigger Voltage,max.		3	V
dv/dt	Critical Rate of Rise of Off-State Voltage,min.	$T_J=125^{\circ}\text{C}, V_{DM}=0.67V_{DRM}$	500	V/us
$R_{th(j-c)}$	Thermal Impedance, max.	Junction to Case	0.40	$^{\circ}\text{C}/\text{W}$
$R_{th(c-f)}$	Thermal Impedance, max.	Case to Fin	0.10	$^{\circ}\text{C}/\text{W}$





Outline:



Circuit Drawing:

